

AMENDMENTS TO THE CLAIMS:

Please amend claims 1 and 22, as shown below.

This listing of claims will replace all prior versions and listings of claims in the
Application:

Claim 1 (currently amended): A semiconductor thin film forming method
comprising:

modifying a predetermined region of a semiconductor thin film by exposing the
semiconductor thin film to a projected light obtained after a light is patterned through plural
patterns formed on a photo mask, said projected light having a beam size in a minor axis
direction in the order of micrometers; and

uniformizing the light to be applied in such a manner that the intensity of ~~[[said]]~~ the
light in a predetermined area on the photo mask distributes within a range of $\pm 11.2\%$ of the
average intensity of ~~[[said]]~~ the light in said area,

wherein spatial distribution of peak intensity of light projected and applied on the
semiconductor thin film is uniformized to an identical extent with the peak intensity of the
intensity distribution on the photo mask.

Claim 2 (withdrawn): A semiconductor thin film forming system for modifying a
predetermined region of a semiconductor thin film by exposing the semiconductor thin film to a
projected light patterned through an exposure pattern formed on a photo mask, said
semiconductor thin film being formed on a substrate held on a substrate stage,

said system comprising a mechanism for sequentially scanning the semiconductor thin
film with the patterned light by individually or concurrently driving the photo mask and the
substrate stage.

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Claim 3 (withdrawn): A semiconductor thin film forming system for modifying a predetermined region of a semiconductor thin film by exposing the semiconductor thin film to a projected light patterned through an exposure pattern formed on a photo mask,

said system comprising a focusing mechanism for obtaining the focus of the patterned light on said predetermined region of the semiconductor thin film when the semiconductor thin film is exposed to the projected patterned light.

Claim 4 (withdrawn): A semiconductor thin film forming system for modifying a predetermined region of a semiconductor thin film by exposing the semiconductor thin film to a projected exposure beam patterned through a pattern formed on a photo mask,

said system comprising a tilt correcting mechanism for correcting the tilt of said patterned exposure beam relative to the semiconductor thin film.

Claim 5 (withdrawn): A semiconductor thin film forming system for modifying a predetermined region of a semiconductor thin film by exposing the semiconductor thin film to a projected exposure beam patterned through a pattern formed on a photo mask,

said system comprising an alignment mechanism for aligning the patterned exposure beam with reference to a mark formed on a substrate, on which said semiconductor thin film is deposited.

Claim 6 (withdrawn): A semiconductor thin film forming system for modifying a predetermined region of a semiconductor thin film by exposing the semiconductor thin film to a projected light patterned through a pattern formed on a photo mask,

said system comprising a mechanism for holding a substrate on a stage, said semiconductor thin film being deposited on said substrate.

Claim 7 (withdrawn): A semiconductor thin film forming system for modifying a predetermined region of a semiconductor thin film by exposing the semiconductor thin film to a projected exposure beam patterned through a pattern formed on a photo mask,
said system comprising a composing mechanism for composing a plurality of laser beams into said exposure beam.

Claim 8 (withdrawn): A system according to claim 7, wherein said plurality of laser beams are first and second laser beams, said composing mechanism composing said first and second laser beams in such a manner that said second laser beam is applied onto the semiconductor thin film with a delay relative to said first laser beam.

Claim 9 (withdrawn); A semiconductor thin film forming system having a process chamber, said process chamber serving to modify a predetermined region of a semiconductor thin film by exposing the semiconductor thin film on a substrate to a projected light patterned through a pattern formed on a photo mask,

said system comprising a mechanism for moving the substrate from said process chamber to a different process chamber without exposing the substrate to the atmosphere.

Claim 10 (withdrawn): A system according to claim 9, wherein said different process chamber is an insulating film forming chamber for the formation of an insulating film on the substrate.

Claim 11 (withdrawn): A system according to claim 9, wherein said different process chamber is a semiconductor film forming chamber for the formation of a semiconductor film on the substrate.

Claim 12 (withdrawn): A system according to claim 9, wherein said different process chamber is a heat treatment chamber for treating the substrate with heat.

Claim 13 (withdrawn): A system according to claim 9, wherein said different process chamber is a plasma treatment chamber for subjecting the substrate to a plasma treatment by treating the substrate with plasma.

Claim 14 (withdrawn): A system according to claim 9, wherein said process chamber is a laser treatment chamber for modifying the predetermined region of the semiconductor thin film by exposing the semiconductor thin film on the substrate to a projected laser beam patterned through the pattern formed on the photo mask, said different process chamber being another laser treatment chamber.

Claim 15 (withdrawn): A system according to claim 9, wherein said different process chamber comprises a plasma generating source for generating plasma in a predetermined area of said different process chamber, said substrate being placed in an area in said different process chamber other than said predetermined area.

Claim 16 (withdrawn): A system according to claim 13, wherein said different process chamber comprises a plasma generating source for generating plasma in a predetermined area of said different process chamber, said different process chamber serving to subject said substrate to said plasma treatment by reacting an excited gas with a different gas, said excited gas being excited by the plasma generated in said predetermined area, said different gas being introduced into said different process chamber without passing through said predetermined area.

Claim 17 (previously presented): The method according to claim 1, wherein said projected light comprises a laser beam.

Claim 18 (previously presented): The method according to claim 17, wherein said laser beam is generated by an excimer laser.

Claim 19 (previously presented): The method according to claim 17, wherein said light is uniformized using a homogenizer, a mask and a projection lens through which said light is applied.

Claim 20 (previously presented): The method according to claim 19, wherein said mask includes a slit for throttling light passed through the homogenizer into a rectangular beam.

Claim 21 (previously presented): A method according to claim 19, wherein a projection lens is used for reducing and projecting a slit image of the mask onto said film.

Claim 22 (currently amended): A semiconductor thin film forming method comprising:

modifying a predetermined region of a semiconductor thin film by exposing the semiconductor thin film to a projected light obtained after a light is patterned through plural patterns formed on a photo mask, said projected light having a beam size in a minor axis direction in the order of micrometers,

wherein [[said]] the light is applied in such a manner that the intensity of [[said]] the light in a predetermined area on the photo mask is distributed within a range of $\pm 11.2\%$ of an average intensity of [[said]] the light in said area.

Claim 23 (new): A semiconductor thin film forming method as claimed in claim 1, wherein said predetermined region of the semiconductor thin film is modified by exposing, at a travel pitch of the order of micrometers, the semiconductor thin film to said projected light.

Claim 24 (new): A semiconductor thin film forming method as claimed in claim 22, wherein said predetermined region of the semiconductor thin film is modified by exposing, at a travel pitch of the order of micrometers, the semiconductor thin film to said projected light.

Claim 25 (new): A semiconductor thin film forming method as claimed in claim 1, wherein said predetermined region of the semiconductor thin film is modified by exposing a target exposure position of the semiconductor thin film to said projected light with a target accuracy of 0.1 μm to 100 μm .

Claim 26 (new): A semiconductor thin film forming method as claimed in claim 22, wherein said predetermined region of the semiconductor thin film is modified by exposing a target exposure position of the semiconductor thin film to said objected light with a target accuracy of 0.1 μm to 100 μm .

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